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Docket No.: 1999P8006 P

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By: 

Date: December 12, 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 09/915,985 Confirmation No: 8172
Applicant : Detlef Hommel et al.
Filed : July 25, 2001
Art Unit : 2811
Examiner : Junghwa M. Im

Docket No. : 1999P8006 P
Customer No. : 24131

INFORMATION DISCLOSURE STATEMENT

12/17/2003 BSAYAS11 00000056 09915985

UNDER 37 C.F.R. 1.97(C)(2)

01 FC:1806

180.00 OP

Hon. Commissioner for Patents

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

United States Patent No. 5,084,804 (Schairer), January 28, 1992, and corresponding German Published Non-Prosecuted Patent Application DE 38 35 942 A1, dated April 26, 1990;

German Published Non-Prosecuted Patent Application DE 31 37 685 A1 (Butenschön), dated April 7, 1983, and English abstract thereof;

H. Wenisch et al.: "Internal photoluminescence and lifetime of light-emitting diodes on conductive ZnSe substrates", *J. Appl. Phys.*, Vol. 82, No. 9, November 1, 1997, pp. 4690-4692;

K. Ohkawa et al.: "ZnSe-Based Laser Diodes and LEDs Grown on ZnSe and GaAs Substrates", *phys. stat.sol. (b)*, No. 202, 1997, pp. 683-693;

Michael Prokesch et al.: "Variable High Conductivity in Homogeneously Iodine Doped ZnSe Bulk Substrates with Simultaneous High Crystallographic Perfection", *2nd Intern. Symp. On Blue Laser and Light Emitting Diodes, Chiba, Japan, September 29 – October 2, 1998, Th-P47, pp. 624-637;*

H. Wenisch et al.: "(Cd,Zn)Se multi-quantum-well LEDs: homoepitaxy on ZnSe substrates and heteroepitaxy on (In,Ga)As/GaAs buffer layers", *Journal of Crystal Growth, No. 159, 1996, pp. 26-31;*

Chi Zhang et al.: "Gallium nitride/conjugated polymer hybrid light emitting diodes: Performance and lifetime", *Journal of Applied Physics, Vol. 84, No. 3, August 1, 1998, pp. 1579-1582;*

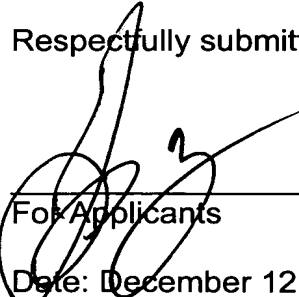
German Examination Report dated November 11, 2003.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

In accordance with 37 C.F.R. 1.97 (c) (2), consideration of this Information Disclosure Statement is requested.

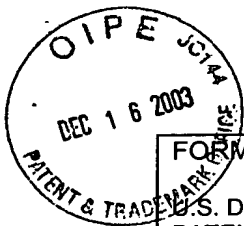
Enclosed is the fee in the amount of \$180.00.

Respectfully submitted,



For Applicants **Gregory L. Mayback**
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FORM PTO-1449 (SUBSTITUTE)

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEINFORMATION DISCLOSURE
STATEMENT BY APPLICANT
(37 CFR 1.98(b))Attorney Docket No.:
1999P8006 PApplic. No.
09/915,985

Applicant

Detlef Hommel et al.

Filing Date
July 25, 2001Group Art Unit
2811

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A	5,084,804	01/28/92	Schairer			
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES NO
	J	38 35 942 A1	04/26/90	Germany			X
	K	31 37 685 A1	04/07/83	Germany			X
	L						
	M						
	N						

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

	O	H. Wenisch et al.: "Internal photoluminescence and lifetime of light-emitting diodes on conductive ZnSe substrates", <i>J. Appl. Phys.</i> , Vol. 82, No. 9, November 1, 1997, pp. 4690-4692
	P	K. Ohkawa et al.: "ZnSe-Based Laser Diodes and LEDs Grown on ZnSe and GaAs Substrates", <i>phys. stat.sol. (b)</i> , No. 202, 1997, pp. 683-693

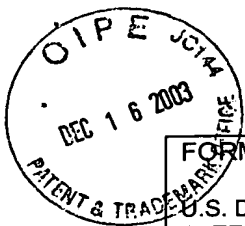
EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



FORM PTO-1449 (SUBSTITUTE) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (37 CFR 1.98(b))				Attorney Docket No.: Applic. No. 1999P8006 P 09/915,985 Applicant Detlef Hommel et al. Filing Date Group Art Unit July 25, 2001 2811			
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	P	H. Wensch et al.: "(Cd,Zn)Se multi-quantum-well LEDs: homoepitaxy on ZnSe substrates and heteroepitaxy on (In,Ga)As/GaAs buffer layers", <i>Journal of Crystal Growth, No. 159, 1996, pp. 26-31</i>					
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